

2SC1471  
 TO3 Silicon NPN High Voltage Switching Transistor

SPECIFICATION

GENERAL DESCRIPTION:

**ELECTRICAL CHARACTERISTICS – CARACTÉRISTIQUES ÉLECTRIQUES \*\***

| SYMBOLS | Min | Typ | Max | UNIT | TEST CONDITIONS – CONDITIONS DE MESURE |
|---------|-----|-----|-----|------|--|
|---------|-----|-----|-----|------|--|

**OFF CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT BLOQUÉ**

|               |     |  |          |    |  |
|---------------|-----|--|----------|----|--|
| $V_{CE0sus}$  | 400 |  |          | V  | $I_B = 0, I_C = 0,2 A, L = 25 mH$  |
| $V_{(BR)EBO}$ | 7   |  | 30       | V  | $I_C = 0, I_B = 0,1 A$   |
| $I_{CEX}$     |     |  | 0,4<br>4 | mA | $T_{case} = 25^{\circ}C$<br>$T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, V_{BE} = -2,5 V$      |
| $I_{CER}$     |     |  | 1<br>8   | mA | $T_{case} = 25^{\circ}C$<br>$T_{case} = 125^{\circ}C$ $V_{CE} = V_{CEX}, R_{BE} \leq 5 \Omega$ |
| $I_{EBO}$     |     |  | 2        | mA | $I_C = 0, V_{EB} = 5 V$  |

**ON CHARACTERISTICS – CARACTÉRISTIQUES A L'ÉTAT CONDUCTEUR**

|               |  |  |          |   |  |
|---------------|--|--|----------|---|--|
| $V_{CEsat}^*$ |  |  | 1,5      | V | $I_C = 20 A, I_B = 4 A$<br>$I_C = 30 A, I_B = 8 A$   |
|               |  |  | 1,5<br>5 | V | $I_C = 16 A, I_B = 3,2 A$<br>$I_C = 24 A, I_B = 5 A$ |
| $V_{BEsat}^*$ |  |  | 1,6      | V | $I_C = 20 A, I_B = 4 A$<br>$I_C = 16 A, I_B = 3,2 A$ |

**DYNAMIC CHARACTERISTICS – CARACTÉRISTIQUES DYNAMIQUES**

|           |  |     |  |     |                                       |
|-----------|--|-----|--|-----|---------------------------------------|
| $f_T$     |  | 5   |  | MHz | $f = 1 MHz, I_C = 1 A, V_{CE} = 10 V$ |
| $C_{22b}$ |  | 500 |  | pF  | $f = 1 MHz, V_{CE} = 10 V$            |

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